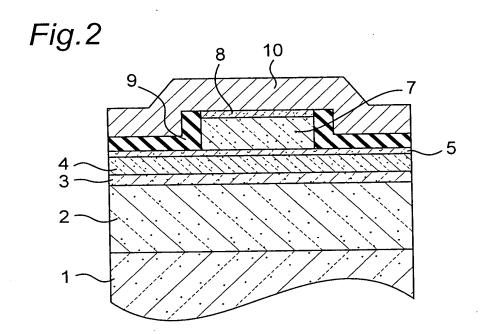
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Fig. 1

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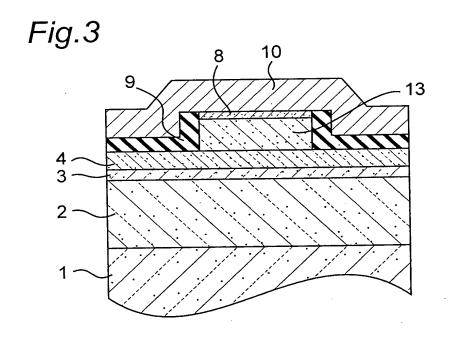


Fig.4

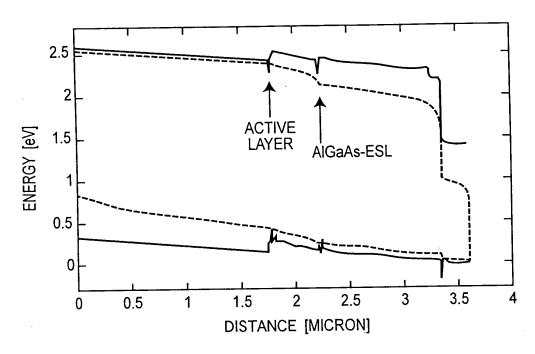
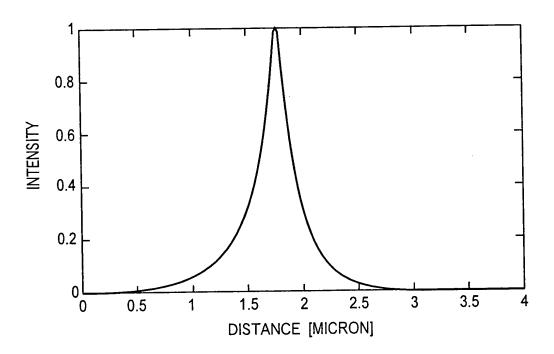


Fig.5

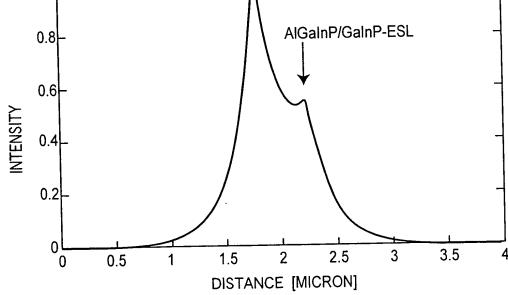


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Fig.6 2 ACTIVE LAYER AlGainP/GainP-ESL ENERGY [eV] 1.5 0.5 0 3.5 2.5 3 1.5 0.5 0 1 DISTANCE [MICRON]

Fig.7 AlGainP/GainP-ESL



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Fig.8

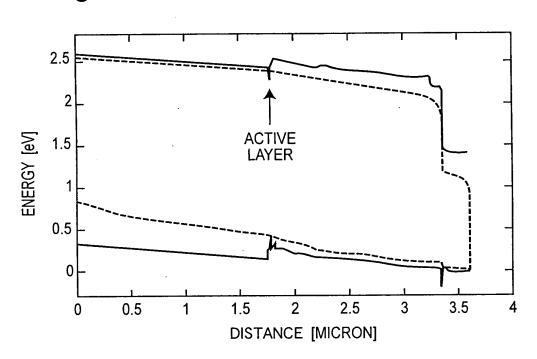
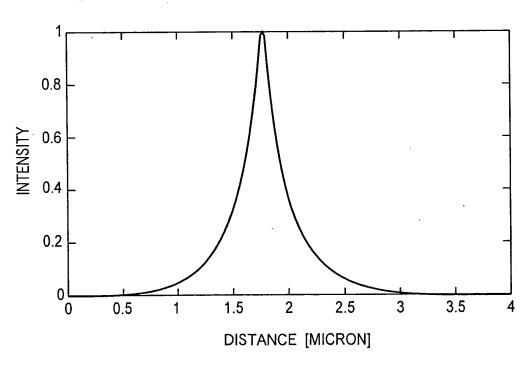


Fig.9



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Fig.10

